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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	672-LBGA
Supplier Device Package	672-LBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8349ezuajd

- On-chip arbitration supporting five masters on PCI1, three masters on PCI2
- Accesses to all PCI address spaces
- Parity supported
- Selectable hardware-enforced coherency
- Address translation units for address mapping between host and peripheral
- Dual address cycle for target
- Internal configuration registers accessible from PCI

- Security engine is optimized to handle all the algorithms associated with IPSec, SSL/TLS, SRTP, IEEE Std. 802.11i®, iSCSI, and IKE processing. The security engine contains four crypto-channels, a controller, and a set of crypto execution units (EUs):
  - Public key execution unit (PKEU) :
    - RSA and Diffie-Hellman algorithms
    - Programmable field size up to 2048 bits
    - Elliptic curve cryptography
    - F2m and F(p) modes
    - Programmable field size up to 511 bits
  - Data encryption standard (DES) execution unit (DEU)
    - DES and 3DES algorithms
    - Two key (K1, K2) or three key (K1, K2, K3) for 3DES
    - ECB and CBC modes for both DES and 3DES
  - Advanced encryption standard unit (AESU)
    - Implements the Rijndael symmetric-key cipher
    - Key lengths of 128, 192, and 256 bits
    - ECB, CBC, CCM, and counter (CTR) modes
  - XOR parity generation accelerator for RAID applications
  - ARC four execution unit (AFEU)
    - Stream cipher compatible with the RC4 algorithm
    - 40- to 128-bit programmable key
  - Message digest execution unit (MDEU)
    - SHA with 160-, 224-, or 256-bit message digest
    - MD5 with 128-bit message digest
    - HMAC with either algorithm
  - Random number generator (RNG)
  - Four crypto-channels, each supporting multi-command descriptor chains
    - Static and/or dynamic assignment of crypto-execution units through an integrated controller
    - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
- Universal serial bus (USB) dual role controller
  - USB on-the-go mode with both device and host functionality

2 Typical power is based on a voltage of V_{DD} = 1.2 V, a junction temperature of T_J = 105°C, and a Dhrystone benchmark application.
3 Thermal solutions may need to design to a value higher than typical power based on the end application, T_A target, and I/O power.
4 Maximum power is based on a voltage of V_{DD} = 1.2 V, worst case process, a junction temperature of T_J = 105°C, and an artificial smoke test.
5 Typical power is based on a voltage of V_{DD} = 1.3 V, a junction temperature of T_J = 105°C, and a Dhrystone benchmark application.
6 Maximum power is based on a voltage of V_{DD} = 1.3 V, worst case process, a junction temperature of T_J = 105°C, and an artificial smoke test.

Table 5 shows the estimated typical I/O power dissipation for MPC8349EA.

Table 5. MPC8349EA Typical I/O Power Dissipation

Interface	Parameter	GV_{DD} (1.8 V)	GV_{DD} (2.5 V)	OV_{DD} (3.3 V)	LV_{DD} (3.3 V)	LV_{DD} (2.5 V)	Unit	Comments
DDR I/O 65% utilization 2.5 V Rs = 20 Ω Rt = 50 Ω 2 pair of clocks	200 MHz, 32 bits	0.31	0.42	—	—	—	W	—
	200 MHz, 64 bits	0.42	0.55	—	—	—	W	—
	266 MHz, 32 bits	0.35	0.5	—	—	—	W	—
	266 MHz, 64 bits	0.47	0.66	—	—	—	W	—
	300 MHz, 32 bits	0.37	0.54	—	—	—	W	—
	300 MHz, 64 bits	0.50	0.7	—	—	—	W	—
	333 MHz, 32 bits	0.39	0.58	—	—	—	W	—
	333 MHz, 64 bits	0.53	0.76	—	—	—	W	—
	400 MHz, 32 bits	0.44	—	—	—	—	—	—
	400 MHz, 64 bits	0.59	—	—	—	—	—	—
PCI I/O load = 30 pF	33 MHz, 64 bits	—	—	0.08	—	—	W	—
	66 MHz, 64 bits	—	—	0.14	—	—	W	—
	33 MHz, 32 bits	—	—	0.04	—	—	W	Multiply by 2 if using 2 ports.
	66 MHz, 32 bits	—	—	0.07	—	—	W	
Local bus I/O load = 25 pF	133 MHz, 32 bits	—	—	0.27	—	—	W	—
	83 MHz, 32 bits	—	—	0.17	—	—	W	—
	66 MHz, 32 bits	—	—	0.14	—	—	W	—
	50 MHz, 32 bits	—	—	0.11	—	—	W	—
TSEC I/O load = 25 pF	MII	—	—	—	0.01	—	W	Multiply by number of interfaces used.
	GMII or TBI	—	—	—	0.06	—	W	
	RGMII or RTBI	—	—	—	—	0.04	W	
USB	12 MHz	—	—	0.01	—	—	W	Multiply by 2 if using 2 ports.
	480 MHz	—	—	0.2	—	—	W	
Other I/O	—	—	—	0.01	—	—	W	—

Table 9. RESET Pins DC Electrical Characteristics[1] (continued)

Parameter	Symbol	Condition	Min	Max	Unit
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

Notes:
1. This table applies for pins $\overline{\text{PORESET}}$, $\overline{\text{HRESET}}$, $\overline{\text{SRESET}}$, and $\overline{\text{QUIESCE}}$.
2. $\overline{\text{HRESET}}$ and $\overline{\text{SRESET}}$ are open drain pins, thus V_{OH} is not relevant for those pins.

5.2 RESET AC Electrical Characteristics

Table 10 provides the reset initialization AC timing specifications of the MPC8349EA.

Table 10. RESET Initialization Timing Specifications

Parameter	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$ or $\overline{\text{SRESET}}$ (input) to activate reset flow	32	—	$t_{PCI\_SYNC\_IN}$	1
Required assertion time of $\overline{\text{PORESET}}$ with stable clock applied to CLKIN when the MPC8349EA is in PCI host mode	32	—	t_{CLKIN}	2
Required assertion time of $\overline{\text{PORESET}}$ with stable clock applied to PCI_SYNC_IN when the MPC8349EA is in PCI agent mode	32	—	$t_{PCI\_SYNC\_IN}$	1
$\overline{\text{HRESET}}$/$\overline{\text{SRESET}}$ assertion (output)	512	—	$t_{PCI\_SYNC\_IN}$	1
$\overline{\text{HRESET}}$ negation to $\overline{\text{SRESET}}$ negation (output)	16	—	$t_{PCI\_SYNC\_IN}$	1
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of $\overline{\text{PORESET}}$ when the MPC8349EA is in PCI host mode	4	—	t_{CLKIN}	2
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of $\overline{\text{PORESET}}$ when the MPC8349EA is in PCI agent mode	4	—	$t_{PCI\_SYNC\_IN}$	1
Input hold time for POR configuration signals with respect to negation of $\overline{\text{HRESET}}$	0	—	ns	—
Time for the MPC8349EA to turn off POR configuration signals with respect to the assertion of $\overline{\text{HRESET}}$	—	4	ns	3
Time for the MPC8349EA to turn on POR configuration signals with respect to the negation of $\overline{\text{HRESET}}$	1	—	$t_{PCI\_SYNC\_IN}$	1, 3

Notes:
1. $t_{PCI\_SYNC\_IN}$ is the clock period of the input clock applied to PCI_SYNC_IN. In PCI host mode, the primary clock is applied to the CLKIN input, and PCI_SYNC_IN period depends on the value of CFG_CLKIN_DIV. See the *MPC8349EA PowerQUICC II Pro Integrated Host Processor Family Reference Manual*.
2. t_{CLKIN} is the clock period of the input clock applied to CLKIN. It is valid only in PCI host mode. See the *MPC8349EA PowerQUICC II Pro Integrated Host Processor Family Reference Manual*.
3. POR configuration signals consist of CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV.

Table 12. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V (continued)

Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to equal 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} cannot exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to equal MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

Table 13 provides the DDR2 capacitance when GV_{DD}(typ) = 1.8 V.

Table 13. DDR2 SDRAM Capacitance for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 14 provides the recommended operating conditions for the DDR SDRAM component(s) when GV_{DD}(typ) = 2.5 V.

Table 14. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.18	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.18	V	—
Output leakage current	I_{OZ}	–9.9	–9.9	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–15.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	15.2	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

6.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 20 shows the DDR and DDR2 output AC timing specifications.

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol [1]	Min	Max	Unit	Notes
ADDR/CMD/MODT output setup with respect to MCK	t_{DDKHAS}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	—		
ADDR/CMD/MODT output hold with respect to MCK	t_{DDKHAX}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	—		
$\overline{MCS}$(n) output setup with respect to MCK	t_{DDKHCS}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	—		
$\overline{MCS}$(n) output hold with respect to MCK	t_{DDKHCX}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	—		
MCK to MDQS Skew	t_{DDKHMH}	–0.6	0.6	ns	4
MDQ/MECC/MDM output setup with respect to MDQS	t_{DDKHDS}, t_{DDKLDS}			ps	5
400 MHz		700	—		
333 MHz		775	—		
266 MHz		1100	—		
200 MHz		1200	—		
MDQ/MECC/MDM output hold with respect to MDQS	t_{DDKHDX}, t_{DDKLDX}			ps	5
400 MHz		700	—		
333 MHz		900	—		
266 MHz		1100	—		
200 MHz		1200	—		
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol [1]	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDKHME}	–0.6	0.6	ns	6

Notes:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output goes invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are set up (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the clock control register is set to adjust the memory clocks by 1/2 applied cycle.
4. t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register and is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these two parameters are set to the same adjustment value. See the *MPC8349EA PowerQUICC II Pro Integrated Host Processor Family Reference Manual* for the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK(n) at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

Figure 6 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

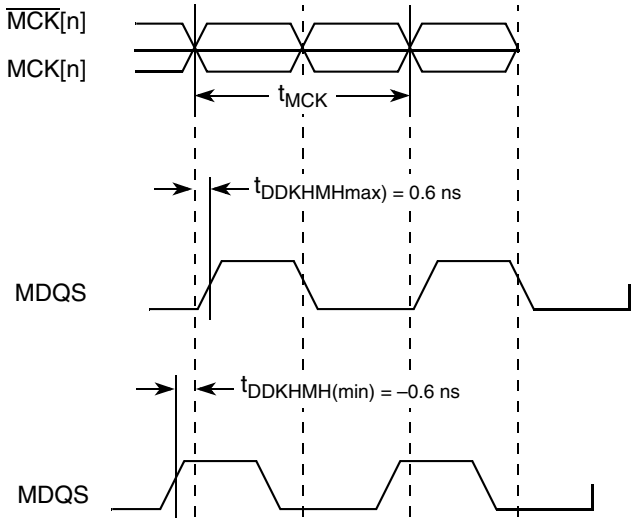


Figure 6. Timing Diagram for t_{DDKHMH}

Table 21. DUART DC Electrical Characteristics (continued)

Parameter	Symbol	Min	Max	Unit
High-level output voltage, I_{OH} = –100 μA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 μA	V_{OL}	—	0.2	V

7.2 DUART AC Electrical Specifications

Table 22 provides the AC timing parameters for the DUART interface of the MPC8349EA.

Table 22. DUART AC Timing Specifications

Parameter	Value	Unit	Notes
Minimum baud rate	256	baud	—
Maximum baud rate	> 1,000,000	baud	1
Oversample rate	16	—	2

Notes:
1. Actual attainable baud rate will be limited by the latency of interrupt processing.
2. The middle of a start bit is detected as the 8th sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16th sample.

8 Ethernet: Three-Speed Ethernet, MII Management

This section provides the AC and DC electrical characteristics for three-speeds (10/100/1000 Mbps) and MII management.

8.1 Three-Speed Ethernet Controller (TSEC)—GMII/MII/TBI/RGMII/RTBI Electrical Characteristics

The electrical characteristics specified here apply to gigabit media independent interface (GMII), the media independent interface (MII), ten-bit interface (TBI), reduced gigabit media independent interface (RGMII), and reduced ten-bit interface (RTBI) signals except management data input/output (MDIO) and management data clock (MDC). The MII, GMII, and TBI interfaces are defined for 3.3 V, and the RGMII and RTBI interfaces are defined for 2.5 V. The RGMII and RTBI interfaces follow the Hewlett-Packard *Reduced Pin-Count Interface for Gigabit Ethernet Physical Layer Device Specification*, Version 1.2a (9/22/2000). The electrical characteristics for MDIO and MDC are specified in Section 8.3, "Ethernet Management Interface Electrical Characteristics."

Table 26. GMII Receive AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
RX_CLK clock rise (20%–80%)	t_{GRXR}	—	—	1.0	ns
RX_CLK clock fall time (80%–20%)	t_{GRXF}	—	—	1.0	ns

Note:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 10 shows the GMII receive AC timing diagram.

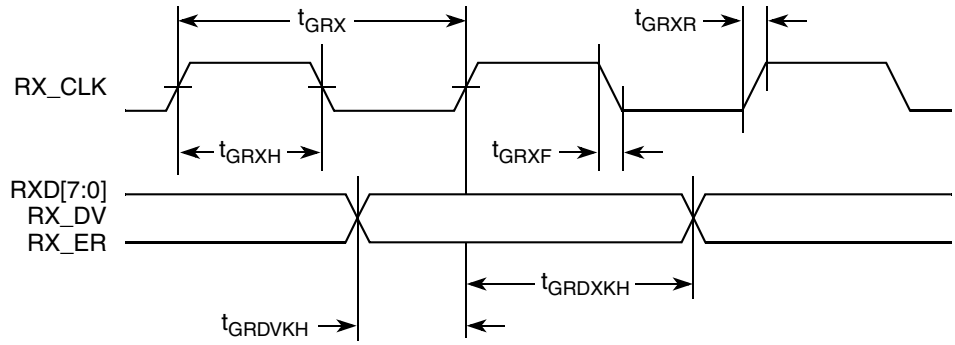


Figure 10. GMII Receive AC Timing Diagram

8.2.2 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.2.1 MII Transmit AC Timing Specifications

Table 27 provides the MII transmit AC timing specifications.

Table 27. MII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns

Table 39. Local Bus General Timing Parameters—DLL Bypass[9]

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	15	—	ns	2
Input setup to local bus clock	t_{LBIVKH}	7	—	ns	3, 4
Input hold from local bus clock	t_{LBIXKH}	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7
Local bus clock to output valid	t_{LBKLOV}	—	3	ns	3
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	4	ns	8

Notes:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to the falling edge of LCLK0 (for all outputs and for $\overline{\text{LGTA}}$ and LUPWAIT inputs) or the rising edge of LCLK0 (for all other inputs).
3. All signals are measured from $OV_{DD}/2$ of the rising/falling edge of LCLK0 to $0.4 \times OV_{DD}$ of the signal in question for 3.3 V signaling levels.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when RCWH[LALE] is set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.
6. $t_{LBOTOT2}$ should be used when RCWH[LALE] is not set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.the
7. $t_{LBOTOT3}$ should be used when RCWH[LALE] is not set and when the load on the LALE output pin equals to the load on the LAD output pins.
8. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
9. DLL bypass mode is not recommended for use at frequencies above 66 MHz.

Figure 20 provides the AC test load for the local bus.

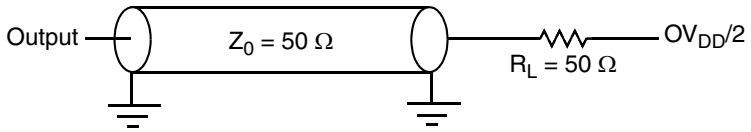


Figure 20. Local Bus C Test Load

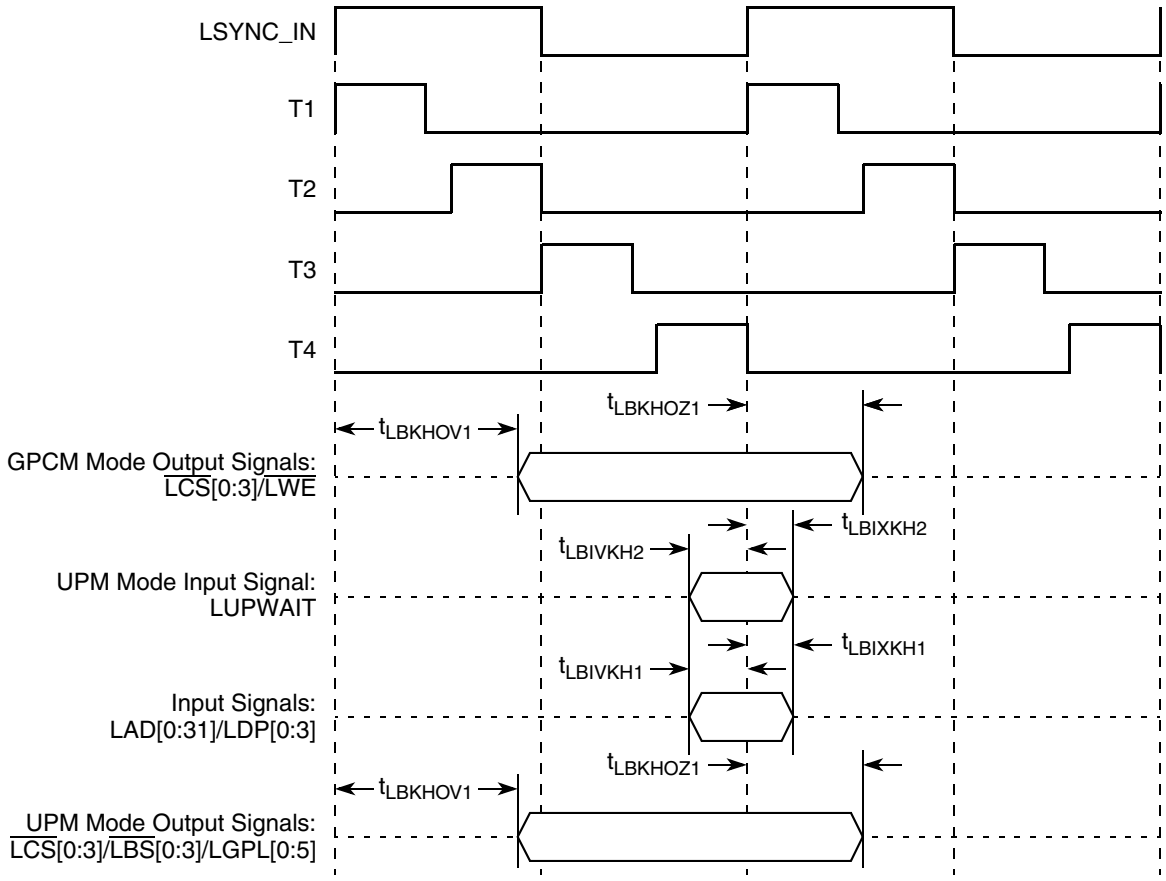


Figure 26. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (DLL Enabled)

11 JTAG

This section describes the DC and AC electrical specifications for the IEEE Std. 1149.1 (JTAG) interface of the MPC8349EA.

11.1 JTAG DC Electrical Characteristics

Table 40 provides the DC electrical characteristics for the IEEE Std. 1149.1 (JTAG) interface of the MPC8349EA.

Table 40. JTAG Interface DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	OV_{DD} – 0.3	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V

Table 41. JTAG AC Timing Specifications (Independent of CLKIN)[1] (continued)

At recommended operating conditions (see Table 2).

Parameter	Symbol[2]	Min	Max	Unit	Notes
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 2 2	 19 9	ns	5, 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50 Ω load (see Figure 18). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design and characterization.

Figure 27 provides the AC test load for TDO and the boundary-scan outputs of the MPC8349EA.

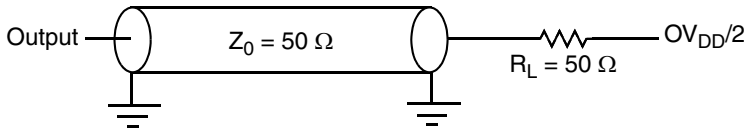


Figure 27. AC Test Load for the JTAG Interface

Figure 28 provides the JTAG clock input timing diagram.

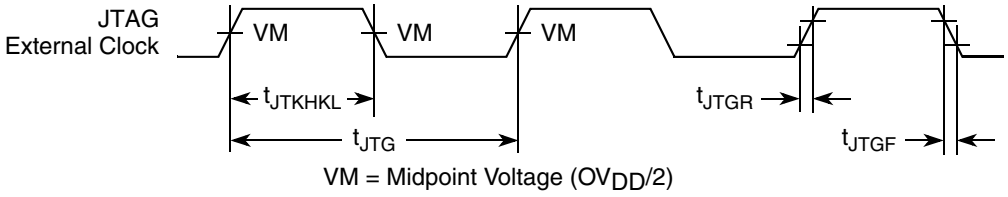


Figure 28. JTAG Clock Input Timing Diagram

Figure 29 provides the $\overline{\text{TRST}}$ timing diagram.

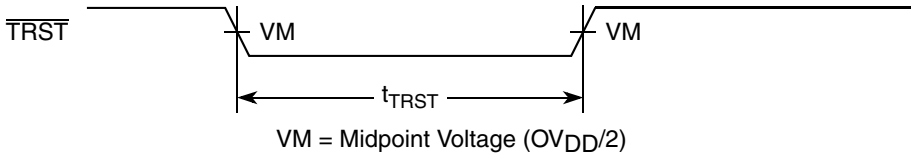


Figure 29. $\overline{\text{TRST}}$ Timing Diagram

17 SPI

This section describes the SPI DC and AC electrical specifications.

17.1 SPI DC Electrical Characteristics

Table 53 provides the SPI DC electrical characteristics.

Table 53. SPI DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

17.2 SPI AC Timing Specifications

Table 54 provides the SPI input and output AC timing specifications.

Table 54. SPI AC Timing Specifications[1]

Parameter	Symbol[2]	Min	Max	Unit
SPI outputs valid—Master mode (internal clock) delay	t_{NIKHOV}	—	6	ns
SPI outputs hold—Master mode (internal clock) delay	t_{NIKHOX}	0.5	—	ns
SPI outputs valid—Slave mode (external clock) delay	t_{NEKHOV}	—	8	ns
SPI outputs hold—Slave mode (external clock) delay	t_{NEKHOX}	2	—	ns
SPI inputs—Master mode (internal clock input setup time	t_{NIIVKH}	4	—	ns
SPI inputs—Master mode (internal clock input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:

1. Output specifications are measured from the 50 percent level of the rising edge of CLKIN to the 50 percent level of the signal. Timings are measured at the pin.
2. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOX} symbolizes the internal timing (NI) for the time SPICLK clock reference (K) goes to the high state (H) until outputs (O) are invalid (X).

Table 55. MPC8349EA (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MBA[2]	H4	O	GV_{DD}	—
MDIC0	AB1	I/O	—	9
MDIC1	AA1	I/O	—	9
Local Bus Controller Interface				
LAD[0:31]	AM13, AP13, AL14, AM14, AN14, AP14, AK15, AJ15, AM15, AN15, AP15, AM16, AL16, AN16, AP16, AL17, AM17, AP17, AK17, AP18, AL18, AM18, AN18, AP19, AN19, AM19, AP20, AK19, AN20, AL20, AP21, AN21	I/O	OV_{DD}	—
LDP[0]/$\overline{\text{CKSTOP\_OUT}}$	AM21	I/O	OV_{DD}	—
LDP[1]/$\overline{\text{CKSTOP\_IN}}$	AP22	I/O	OV_{DD}	—
LDP[2]/$\overline{\text{LCS}}$[4]	AN22	I/O	OV_{DD}	—
LDP[3]/$\overline{\text{LCS}}$[5]	AM22	I/O	OV_{DD}	—
LA[27:31]	AK21, AP23, AN23, AP24, AK22	O	OV_{DD}	—
$\overline{\text{LCS}}$[0:3]	AN24, AL23, AP25, AN25	O	OV_{DD}	—
$\overline{\text{LWE}}$[0:3]/LSDDQM[0:3]/$\overline{\text{LBS}}$[0:3]	AK23, AP26, AL24, AM25	O	OV_{DD}	—
LBCTL	AN26	O	OV_{DD}	—
LALE	AK24	O	OV_{DD}	—
LGPL0/LSDA10/cfg_reset_source0	AP27	I/O	OV_{DD}	—
LGPL1/$\overline{\text{LSDWE}}$/cfg_reset_source1	AL25	I/O	OV_{DD}	—
LGPL2/$\overline{\text{LSDRAS}}$/$\overline{\text{LOE}}$	AJ24	O	OV_{DD}	—
LGPL3/$\overline{\text{LSDCAS}}$/cfg_reset_source2	AN27	I/O	OV_{DD}	—
LGPL4/$\overline{\text{LGTA}}$/LUPWAIT/LPBSE	AP28	I/O	OV_{DD}	12
LGPL5/cfg_clkin_div	AL26	I/O	OV_{DD}	—
LCKE	AM27	O	OV_{DD}	—
LCLK[0:2]	AN28, AK26, AP29	O	OV_{DD}	—
LSYNC_OUT	AM12	O	OV_{DD}	—
LSYNC_IN	AJ10	I	OV_{DD}	—
General Purpose I/O Timers				
GPIO1[0]/$\overline{\text{DMA\_DREQ0}}$/GTM1_TIN1/ GTM2_TIN2	F24	I/O	OV_{DD}	—
GPIO1[1]/$\overline{\text{DMA\_DACK0}}$/ $\overline{\text{GTM1\_TGATE1}}$/$\overline{\text{GTM2\_TGATE2}}$	E24	I/O	OV_{DD}	—

Table 55. MPC8349EA (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GPIO1[2]/DMA_DDONE0/ GTM1_TOUT1	B25	I/O	OV_{DD}	—
GPIO1[3]/DMA_DREQ1/GTM1_TIN2/ GTM2_TIN1	D24	**I/O**	OV_{DD}	—
GPIO1[4]/DMA_DACK1/ GTM1_TGATE2/GTM2_TGATE1	A25	**I/O**	OV_{DD}	—
GPIO1[5]/DMA_DDONE1/ GTM1_TOUT2/GTM2_TOUT1	B24	**I/O**	OV_{DD}	—
GPIO1[6]/DMA_DREQ2/GTM1_TIN3/ GTM2_TIN4	A24	**I/O**	OV_{DD}	—
GPIO1[7]/DMA_DACK2/ GTM1_TGATE3/GTM2_TGATE4	D23	**I/O**	OV_{DD}	—
GPIO1[8]/DMA_DDONE2/ GTM1_TOUT3	B23	**I/O**	OV_{DD}	—
GPIO1[9]/DMA_DREQ3/GTM1_TIN4/ GTM2_TIN3	A23	**I/O**	OV_{DD}	—
GPIO1[10]/DMA_DACK3/ GTM1_TGATE4/GTM2_TGATE3	F22	**I/O**	OV_{DD}	—
GPIO1[11]/DMA_DDONE3/ GTM1_TOUT4/GTM2_TOUT3	E22	**I/O**	OV_{DD}	—
USB Port 1				
MPH1_D0_ENABLEN/ DR_D0_ENABLEN	A26	I/O	OV_{DD}	—
MPH1_D1_SER_TXD/ DR_D1_SER_TXD	B26	I/O	OV_{DD}	—
MPH1_D2_VMO_SE0/ DR_D2_VMO_SE0	D25	I/O	OV_{DD}	—
MPH1_D3_SPEED/DR_D3_SPEED	A27	I/O	OV_{DD}	—
MPH1_D4_DP/DR_D4_DP	B27	I/O	OV_{DD}	—
MPH1_D5_DM/DR_D5_DM	C27	I/O	OV_{DD}	—
MPH1_D6_SER_RCV/ DR_D6_SER_RCV	D26	I/O	OV_{DD}	—
MPH1_D7_DRVVBUS/ DR_D7_DRVVBUS	E26	I/O	OV_{DD}	—
MPH1_NXT/DR_SESS_VLD_NXT	D27	I	OV_{DD}	—
MPH1_DIR_DPPULLUP/ DR_XCVR_SEL_DPPULLUP	A28	I/O	OV_{DD}	—
MPH1_STP_SUSPEND/ DR_STP_SUSPEND	F26	O	OV_{DD}	—

Table 55. MPC8349EA (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MPH1_PWRFAULT/ DR_RX_ERROR_PWRFAULT	E27	I	OV_{DD}	—
MPH1_PCTL0/DR_TX_VALID_PCTL0	A29	O	OV_{DD}	—
MPH1_PCTL1/DR_TX_VALIDH_PCTL1	D28	O	OV_{DD}	—
MPH1_CLK/DR_CLK	B29	I	OV_{DD}	—
USB Port 0				
MPH0_D0_ENABLEN/ DR_D8_CHGVBUS	C29	I/O	OV_{DD}	—
MPH0_D1_SER_TXD/ DR_D9_DCHGVBUS	A30	I/O	OV_{DD}	—
MPH0_D2_VMO_SE0/DR_D10_DPPD	E28	I/O	OV_{DD}	—
MPH0_D3_SPEED/DR_D11_DMMD	B30	I/O	OV_{DD}	—
MPH0_D4_DP/DR_D12_VBUS_VLD	C30	I/O	OV_{DD}	—
MPH0_D5_DM/DR_D13_SESS_END	A31	I/O	OV_{DD}	—
MPH0_D6_SER_RCV/DR_D14	B31	I/O	OV_{DD}	—
MPH0_D7_DRVVBUS/ DR_D15_IDPULLUP	C31	I/O	OV_{DD}	—
MPH0_NXT/DR_RX_ACTIVE_ID	B32	I	OV_{DD}	—
MPH0_DIR_DPPULLUP/DR_RESET	A32	I/O	OV_{DD}	—
MPH0_STP_SUSPEND/ DR_TX_READY	A33	I/O	OV_{DD}	—
MPH0_PWRFAULT/DR_RX_VALIDH	C32	I	OV_{DD}	—
MPH0_PCTL0/DR_LINE_STATE0	D31	I/O	OV_{DD}	—
MPH0_PCTL1/DR_LINE_STATE1	E30	I/O	OV_{DD}	—
MPH0_CLK/DR_RX_VALID	B33	I	OV_{DD}	—
Programmable Interrupt Controller				
$\overline{\text{MCP\_OUT}}$	AN33	O	OV_{DD}	2
$\overline{\text{IRQ}}$0/$\overline{\text{MCP_IN}}$/GPIO2[12]	C19	I/O	OV_{DD}	—
$\overline{\text{IRQ}}$[1:5]/GPIO2[13:17]	C22, A22, D21, C21, B21	I/O	OV_{DD}	—
$\overline{\text{IRQ}}$[6]/GPIO2[18]/$\overline{\text{CKSTOP\_OUT}}$	A21	I/O	OV_{DD}	—
$\overline{\text{IRQ}}$[7]/GPIO2[19]/$\overline{\text{CKSTOP\_IN}}$	C20	I/O	OV_{DD}	—
Ethernet Management Interface				
EC_MDC	A7	O	LV_{DD1}	—
EC_MDIO	E9	I/O	LV_{DD1}	11

Table 55. MPC8349EA (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Gigabit Reference Clock				
EC_GTX_CLK125	C8	I	LV_{DD1}	—
Three-Speed Ethernet Controller (Gigabit Ethernet 1)				
TSEC1_COL/GPIO2[20]	A17	I/O	OV_{DD}	—
TSEC1_CRS/GPIO2[21]	F12	I/O	LV_{DD1}	—
TSEC1_GTX_CLK	D10	O	LV_{DD1}	3
TSEC1_RX_CLK	A11	I	LV_{DD1}	—
TSEC1_RX_DV	B11	I	LV_{DD1}	—
TSEC1_RX_ER/GPIO2[26]	B17	I/O	OV_{DD}	—
TSEC1_RXD[7:4]/GPIO2[22:25]	B16, D16, E16, F16	I/O	OV_{DD}	—
TSEC1_RXD[3:0]	E10, A8, F10, B8	I	LV_{DD1}	—
TSEC1_TX_CLK	D17	I	OV_{DD}	—
TSEC1_TXD[7:4]/GPIO2[27:30]	A15, B15, A14, B14	I/O	OV_{DD}	—
TSEC1_TXD[3:0]	A10, E11, B10, A9	O	LV_{DD1}	10
TSEC1_TX_EN	B9	O	LV_{DD1}	—
TSEC1_TX_ER/GPIO2[31]	A16	I/O	OV_{DD}	—
Three-Speed Ethernet Controller (Gigabit Ethernet 2)				
TSEC2_COL/GPIO1[21]	C14	I/O	OV_{DD}	—
TSEC2_CRS/GPIO1[22]	D6	I/O	LV_{DD2}	—
TSEC2_GTX_CLK	A4	O	LV_{DD2}	—
TSEC2_RX_CLK	B4	I	LV_{DD2}	—
TSEC2_RX_DV/GPIO1[23]	E6	I/O	LV_{DD2}	—
TSEC2_RXD[7:4]/GPIO1[26:29]	A13, B13, C13, A12	I/O	OV_{DD}	—
TSEC2_RXD[3:0]/GPIO1[13:16]	D7, A6, E8, B7	I/O	LV_{DD2}	—
TSEC2_RX_ER/GPIO1[25]	D14	I/O	OV_{DD}	—
TSEC2_TXD[7]/GPIO1[31]	B12	I/O	OV_{DD}	—
TSEC2_TXD[6]/ DR_XCVR_TERM_SEL	C12	O	OV_{DD}	—
TSEC2_TXD[5]/ DR_UTMI_OPMODE1	D12	O	OV_{DD}	—
TSEC2_TXD[4]/ DR_UTMI_OPMODE0	E12	O	OV_{DD}	—
TSEC2_TXD[3:0]/GPIO1[17:20]	B5, A5, F8, B6	I/O	LV_{DD2}	—

Table 61. e300 Core PLL Configuration

RCWL[COREPLL]			*core_clk* : *csb_clk* Ratio	VCO Divider[1]
0–1	**2–5**	**6**		
nn	**0000**	n	PLL bypassed (PLL off, *csb_clk* clocks core directly)	PLL bypassed (PLL off, *csb_clk* clocks core directly)
00	**0001**	0	1:1	2
01	**0001**	0	1:1	4
10	**0001**	0	1:1	8
11	**0001**	0	1:1	8
00	**0001**	1	1.5:1	2
01	**0001**	1	1.5:1	4
10	**0001**	1	1.5:1	8
11	**0001**	1	1.5:1	8
00	**0010**	0	2:1	2
01	**0010**	0	2:1	4
10	**0010**	0	2:1	8
11	**0010**	0	2:1	8
00	**0010**	1	2.5:1	2
01	**0010**	1	2.5:1	4
10	**0010**	1	2.5:1	8
11	**0010**	1	2.5:1	8
00	**0011**	0	3:1	2
01	**0011**	0	3:1	4
10	**0011**	0	3:1	8
11	**0011**	0	3:1	8

[1] Core VCO frequency = core frequency × VCO divider. The VCO divider must be set properly so that the core VCO frequency is in the range of 800–1800 MHz.

Heat sink vendors include the following list:

Aavid Thermalloy 603-224-9988
80 Commercial St.
Concord, NH 03301
Internet: www.aavidthermalloy.com

Alpha Novatech 408-567-8082
473 Sapena Ct. #12
Santa Clara, CA 95054
Internet: www.alphanovatech.com

International Electronic Research Corporation (IERC) 818-842-7277
413 North Moss St.
Burbank, CA 91502
Internet: www.ctscorp.com

Millennium Electronics (MEI) 408-436-8770
Loroco Sites
671 East Brokaw Road
San Jose, CA 95112
Internet: www.mei-thermal.com

Tyco Electronics 800-522-2800
Chip Coolers™
P.O. Box 3668
Harrisburg, PA 17105-3668
Internet: www.chipcoolers.com

Wakefield Engineering 603-635-5102
33 Bridge St.
Pelham, NH 03076
Internet: www.wakefield.com

Interface material vendors include the following:

Chomerics, Inc. 781-935-4850
77 Dragon Ct.
Woburn, MA 01801
Internet: www.chomerics.com

Dow-Corning Corporation 800-248-2481
Dow-Corning Electronic Materials
P.O. Box 994
Midland, MI 48686-0997
Internet: www.dowcorning.com

Shin-Etsu MicroSi, Inc. 888-642-7674
10028 S. 51st St.
Phoenix, AZ 85044
Internet: www.microsi.com

$V_2 = (1 \div (1/R_1 + 1/R_2)) \times I_{source}$. Solving for the output impedance gives $R_{source} = R_{term} \times (V_1 \div V_2 - 1)$. The drive current is then $I_{source} = V_1 \div R_{source}$.

Table 65 summarizes the signal impedance targets. The driver impedance are targeted at minimum V_{DD}, nominal OV_{DD}, 105°C.

Table 65. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI Signals (Not Including PCI Output Clocks)	PCI Output Clocks (Including PCI_SYNC_OUT)	DDR DRAM	Symbol	Unit
R_N	42 Target	25 Target	42 Target	20 Target	Z_0	W
R_P	42 Target	25 Target	42 Target	20 Target	Z_0	W
Differential	NA	NA	NA	NA	Z_{DIFF}	W

Note: Nominal supply voltages. See Table 1, T_j = 105°C.

21.6 Configuration Pin Multiplexing

The MPC8349EA power-on configuration options can be set through external pull-up or pull-down resistors of 4.7 kΩ on certain output pins (see the customer-visible configuration pins). These pins are used as output only pins in normal operation.

However, while $\overline{\text{HRESET}}$ is asserted, these pins are treated as inputs, and the value on these pins is latched when $\overline{\text{PORESET}}$ deasserts. Then the input receiver is disabled and the I/O circuit takes on its normal function. Careful board layout with stubless connections to these pull-up/pull-down resistors coupled with the large value of the pull-up/pull-down resistor should minimize the disruption of signal quality or speed for the output pins.

21.7 Pull-Up Resistor Requirements

The MPC8349EA requires high resistance pull-up resistors (10 kΩ is recommended) on open-drain pins, including I^2C pins, and IPIC interrupt pins.

For more information on required pull-up resistors and the connections required for the JTAG interface, refer to application note AN2931, “PowerQUICC Design Checklist.”

22 Ordering Information

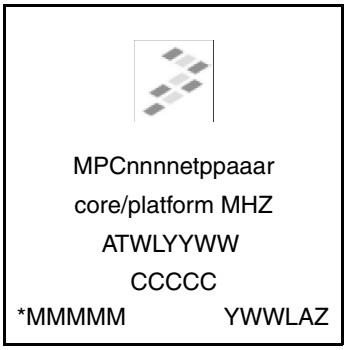
This section presents ordering information for the device discussed in this document, and it shows an example of how the parts are marked.

NOTE

The information in this document is accurate for revision 3.x silicon and later (in other words, for orderable part numbers ending in A or B). For information on revision 1.1 silicon and earlier versions, see the *MPC8349E PowerQUICC II Pro Integrated Host Processor Hardware Specifications* (Document Order No. MPC8349EEC).

22.2 Part Marking

Parts are marked as in the example shown in Figure 44.



Notes:
ATWLYYWW is the traceability code.
CCCCC is the country code.
MMMMM is the mask number.
YWWLAZ is the assembly traceability code.

Figure 44. Freescale Part Marking for TBGA Devices

23 Document Revision History

This table provides a revision history of this document.

Table 68. Document Revision History

Rev. Number	Date	Substantive Change(s)
13	09/2011	• In Section 2.2, "Power Sequencing," added Section 2.2.1, "Power-Up Sequencing" and Figure 4. • In Table 25, Table 29 and Table 31, removed the GTX_CLK125. • In Table 34, updated t_{MDKHDX} Max value from 170ns to 70ns.
12	11/2010	• In Table 55 added note for pin LGPL4. • In Section 21.7, "Pull-Up Resistor Requirements, updated the list of open drain type pins.
11	05/2010	• In Table 25 through Table 30, changed V_{IL}(min) to V_{IH}(max) to (20%–80%). • Added Table 8, "EC_GTX_CLK125 AC Timing Specifications."
10	5/2009	• In Table 57, updated frequency for max csb_clk to 333 MHz and DDR2, from 100-200 to 100-133 at core frequency = 533MHz. • In Section 18.1, "Package Parameters for the MPC8349EA TBGA, changed solder ball for TBGA and PBGA from 95.5 Sn/0.5 Cu/4 Ag to 96.5 Sn/3.5 Ag. • In Table 66, footnote 1, changed 667(TBGA) to 533(TBGA). footnote 4, added data rate for DDR1 and DDR2.